MY3400A

30V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

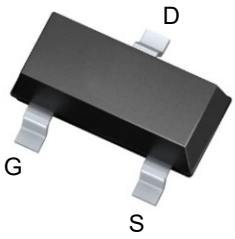
The MY3400A is the high cell density trenched N-CH MOSFET,which provides excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load s witch applications.

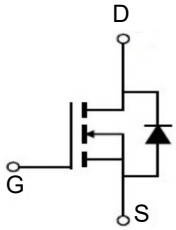
Features

V_{DSS}	30	V
I_D	5.8	A
$R_{DS(ON)}$(atV_{GS}=10V)	<24	mΩ
$R_{DS(ON)}$(atV_{GS}=4.5V)	<28	mΩ

Application

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY3400A	SOT-23-3L	X0BR	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	6.0	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	4.2	A
I_{DM}	Pulsed Drain Current[2]	23.4	A
P_D@T_A=25℃	Total Power Dissipation[3]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	92	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Case[1]	---	---	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.5	0.9	1.4	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}=10V, I_D=4.2A	-	20	24	mΩ
		V_{GS}=4.5V, I_D=4A	-	24	28	
		V_{GS}=2.5V, I_D=1A	-	35	50	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1.0MHz	-	602	-	pF
C_{oss}	Output Capacitance		-	56	-	pF
C_{rss}	Reverse Transfer Capacitance		-	42	-	pF
Q_g	Total Gate Charge	V_{DS}=15V, I=4A, V_{GS}=4.5V	-	4.8	-	nC
Q_{gs}	Gate-Source Charge		-	1.2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	1.7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V, I_D=4A, R_{GEN}=3Ω, V_{GS}=4.5V	-	12	-	ns
t_r	Turn-on Rise Time		-	52	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	17	-	ns
t_f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6.0	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	23.2	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=5.8A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Electrical and Thermal Characteristics

Figure1 : Output Characteristics

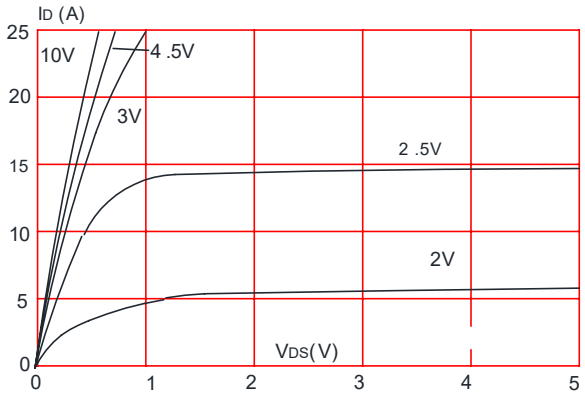


Figure 2 : Typical Transfer Characteristics

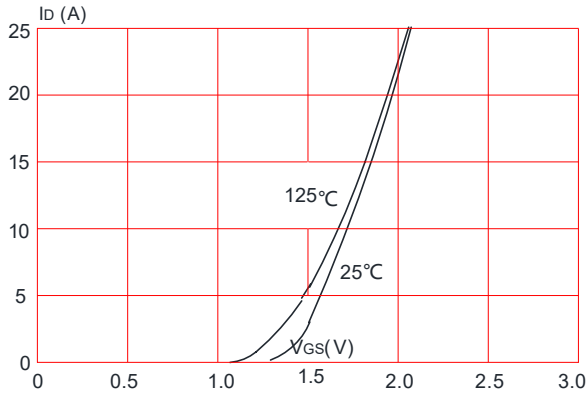


Figure 3 : On- resistance vs . Drain Current

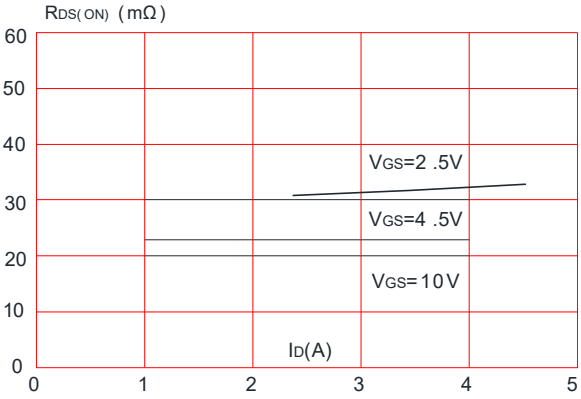


Figure 4 : Body Diode Characteristics

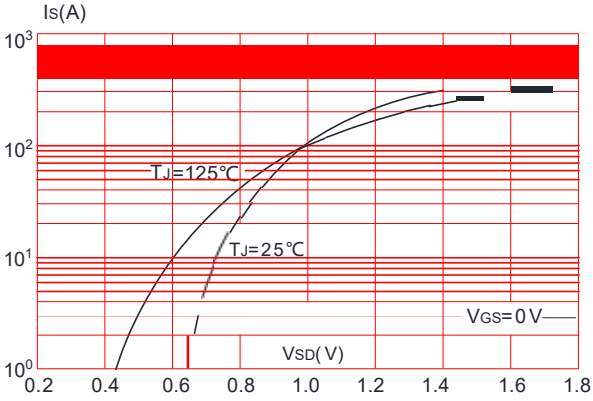


Figure 5 : Gate Charge Characteristics

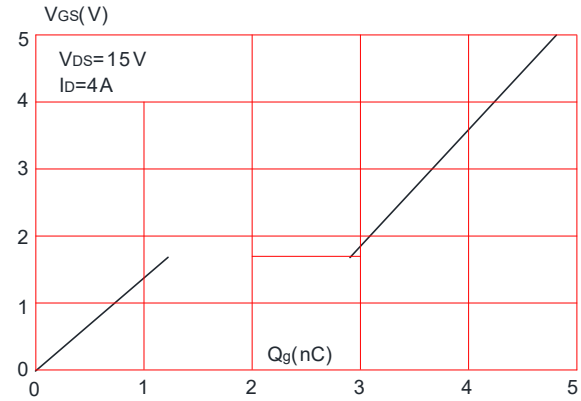


Figure 6 : Capacitance Characteristics

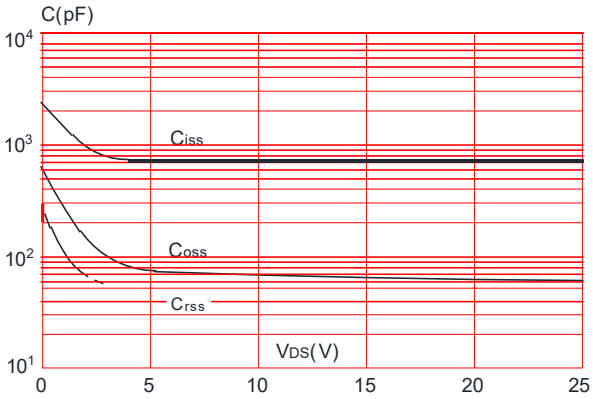


Figure 7 : Normalized Breakdown Voltage vs . Junction Temperature

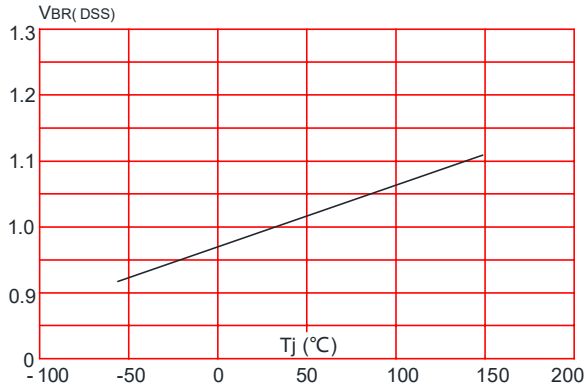


Figure 8: Normalized on Resistance vs . Junction Temperature

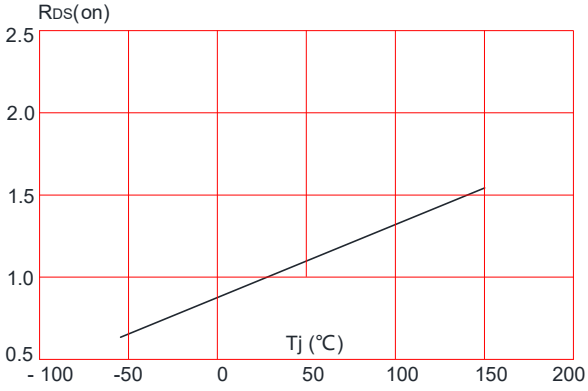


Figure 9: Maximum Safe Operating Area

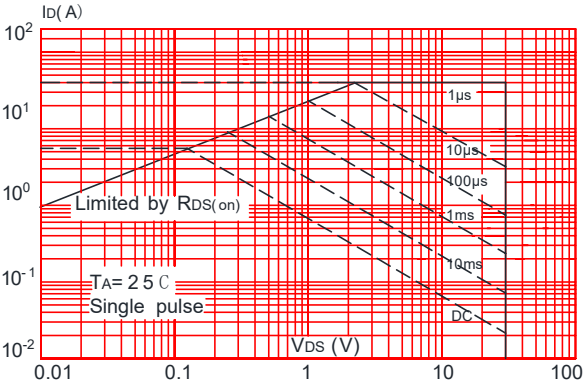


Figure 10: Maximum Continuous Drain Current vs . Case Temperature

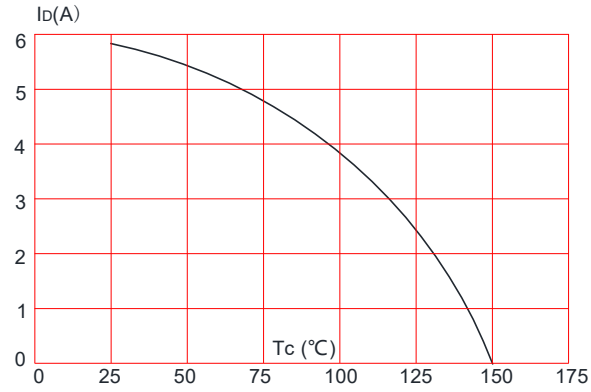
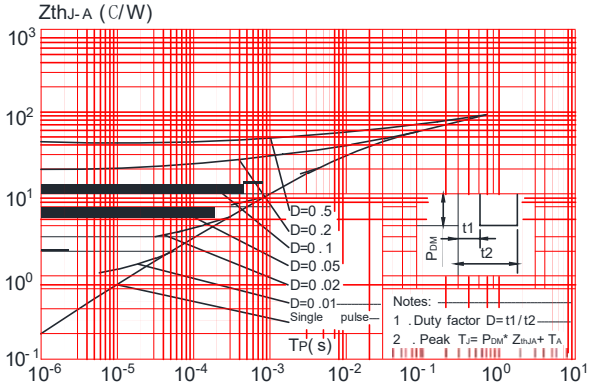
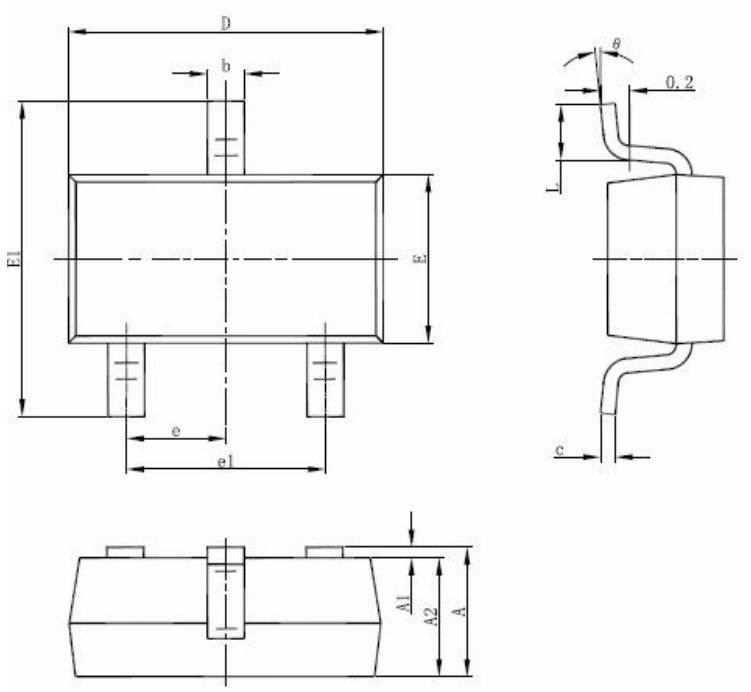


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data-SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°